

SWITCHING  
 N-CHANNEL POWER MOS FET

DESCRIPTION

The  $\mu$ PA1743TP is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for high voltage applications such as DC/DC converter.

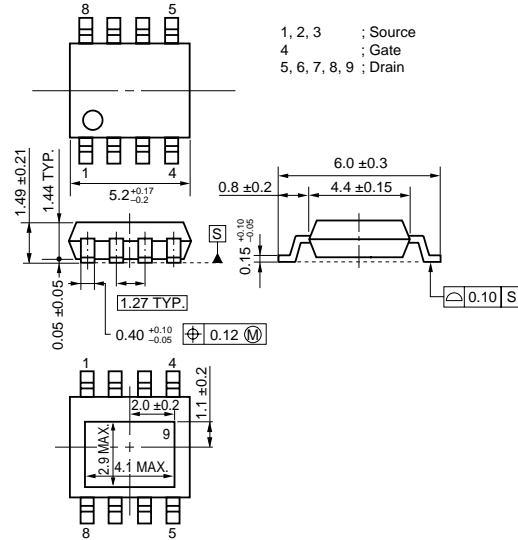
FEATURES

- High voltage:  $V_{BSS} = 250$  V
- Gate voltage rating:  $\pm 30$  V
- Low on-state resistance  
 $R_{DS(on)} = 0.45 \Omega$  MAX. ( $V_{GS} = 10$  V,  $I_D = 4.0$  A)
- Low input capacitance  
 $C_{iss} = 570$  pF TYP. ( $V_{DS} = 10$  V,  $V_{GS} = 0$  V)
- Built-in gate protection diode
- Small and surface mount package (Power HSOP8)

ORDERING INFORMATION

PART NUMBER	PACKAGE
$\mu$ PA1743TP	Power HSOP8

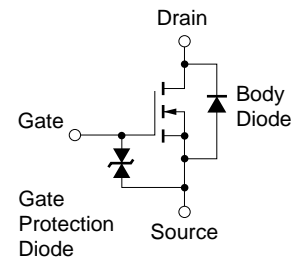
PACKAGE DRAWING (Unit: mm)



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted. All terminals are connected.)

Drain to Source Voltage ( $V_{GS} = 0$ V)	$V_{DSS}$	250	V
Gate to Source Voltage ( $V_{DS} = 0$ V)	$V_{GSS}$	$\pm 30$	V
Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )	$I_{D(DC)}$	$\pm 8.0$	A
Drain Current (pulse) <sup>Note1</sup>	$I_{D(pulse)}$	$\pm 24$	A
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_{T1}$	26	W
Total Power Dissipation ( $T_A = 25^\circ\text{C}$ ) <sup>Note2</sup>	$P_{T2}$	1.0	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Single Avalanche Current <sup>Note3</sup>	$I_{AS}$	8.0	A
Single Avalanche Energy <sup>Note3</sup>	$E_{AS}$	6.4	mJ
Repetitive Avalanche Current <sup>Note4</sup>	$I_{AR}$	8.0	A
Repetitive Pulse Avalanche Energy <sup>Note4</sup>	$E_{AR}$	6.4	mJ

EQUIVALENT CIRCUIT



- Notes**
1.  $PW \leq 10 \mu\text{s}$ , Duty Cycle  $\leq 1\%$
  2. Mounted on a glass epoxy board of 1 inch x 1 inch x 0.8 mm
  3. Starting  $T_{ch} = 25^\circ\text{C}$ ,  $V_{DD} = 125$  V,  $R_G = 25 \Omega$ ,  $L = 100 \mu\text{H}$ ,  $V_{GS} = 20 \rightarrow 0$  V
  4.  $T_{ch(peak)} \leq 150^\circ\text{C}$ ,  $L = 100 \mu\text{H}$

**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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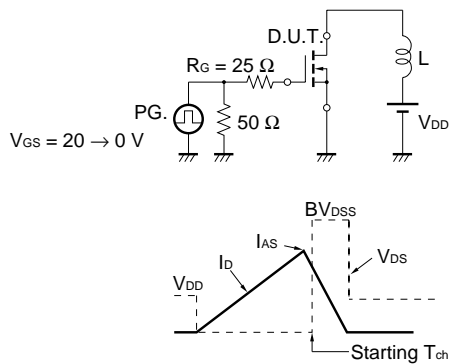
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**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise noted. All terminals are connected.)**

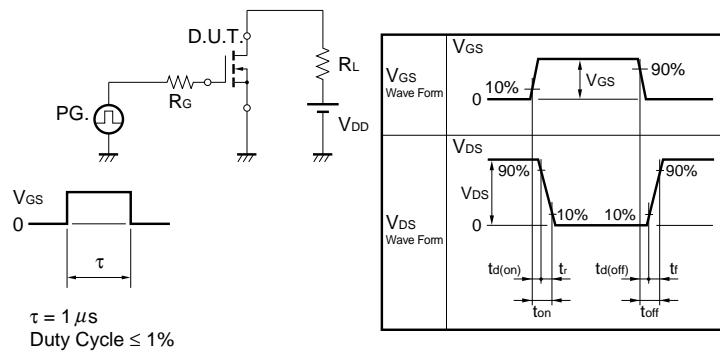
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V			10	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V			±10	μA
Gate Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.5	3.5	4.5	V
Forward Transfer Admittance <b>Note</b>	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 4.0 A	3	5		S
Drain to Source On-state Resistance <b>Note</b>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.0 A		0.34	0.45	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V		570		pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		120		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1 MHz		50		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 125 V, I <sub>D</sub> = 4.0 A		12		ns
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = 10 V		9		ns
Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 10 Ω		28		ns
Fall Time	t <sub>f</sub>			8		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = 200 V		17		nC
Gate to Source Charge	Q <sub>GS</sub>	V <sub>GS</sub> = 10 V		3		nC
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = 8.0 A		9		nC
Body Diode Forward Voltage <b>Note</b>	V <sub>F(S-D)</sub>	I <sub>F</sub> = 8.0 A, V <sub>GS</sub> = 0 V		0.9	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 8.0 A, V <sub>GS</sub> = 0 V		140		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100 A/μs		610		nC

**Note** Pulsed: PW ≤ 800 μs, Duty Cycle ≤ 2%

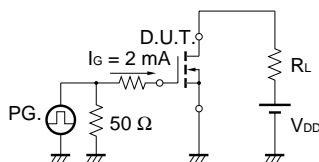
**TEST CIRCUIT 1 AVALANCHE CAPABILITY**



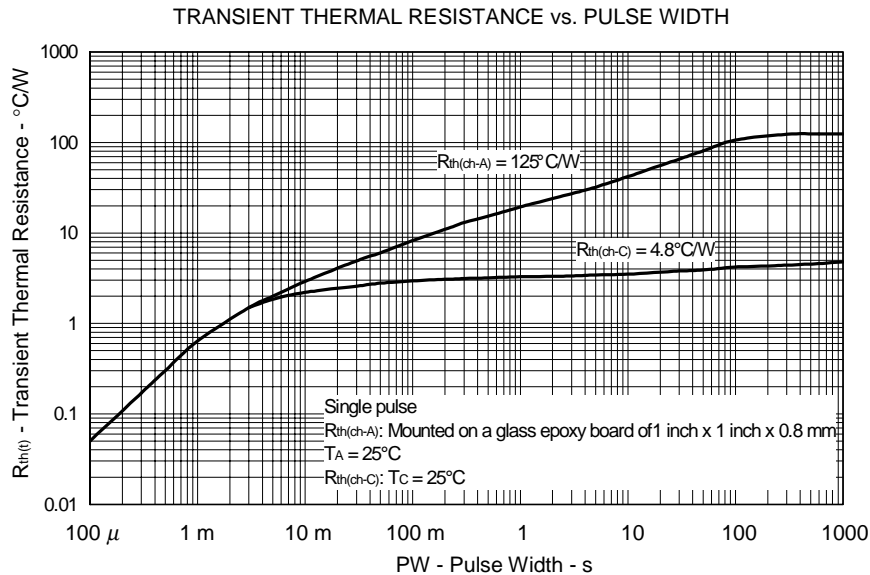
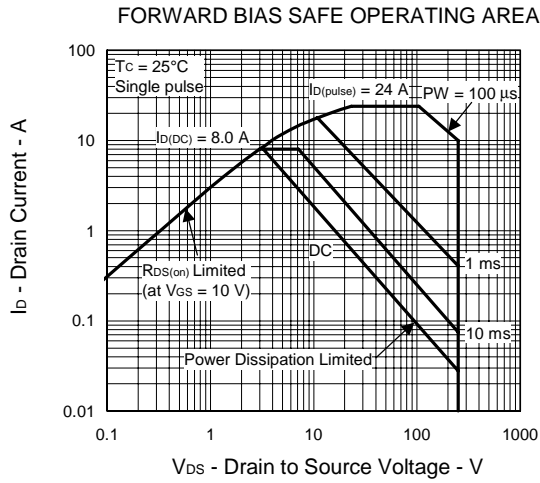
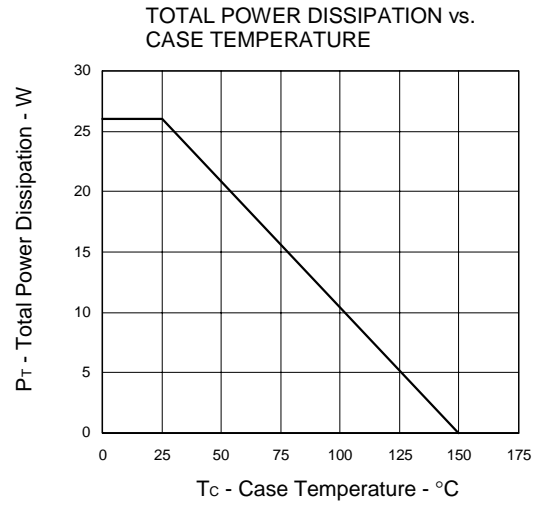
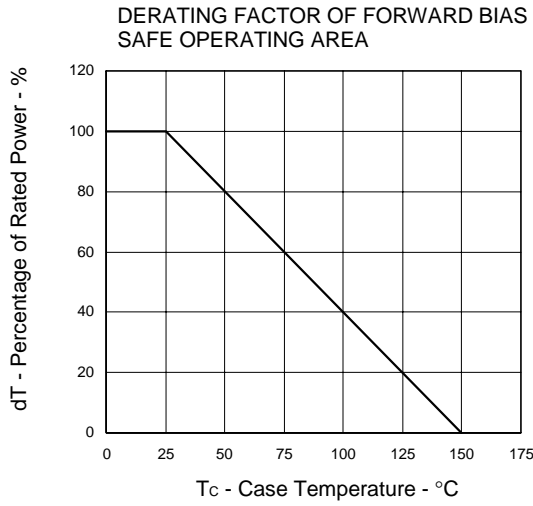
**TEST CIRCUIT 2 SWITCHING TIME**



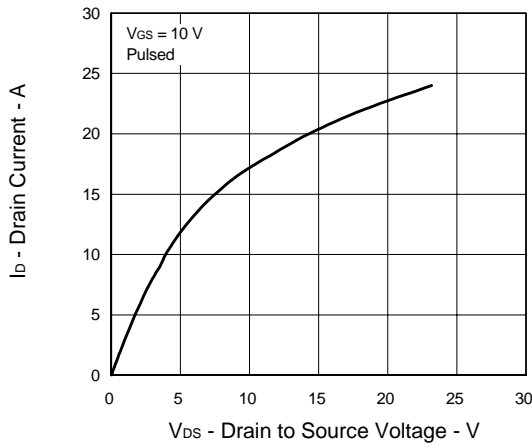
**TEST CIRCUIT 3 GATE CHARGE**



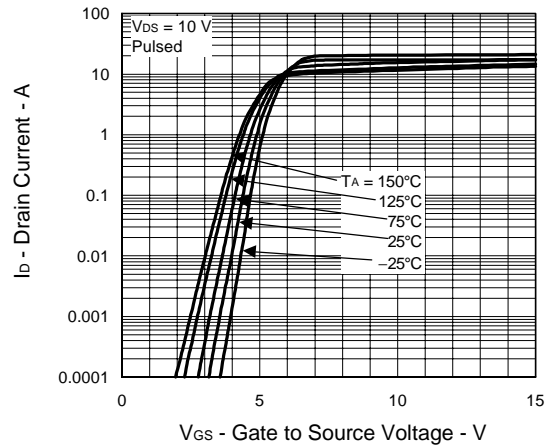
TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted. All terminals are connected.)



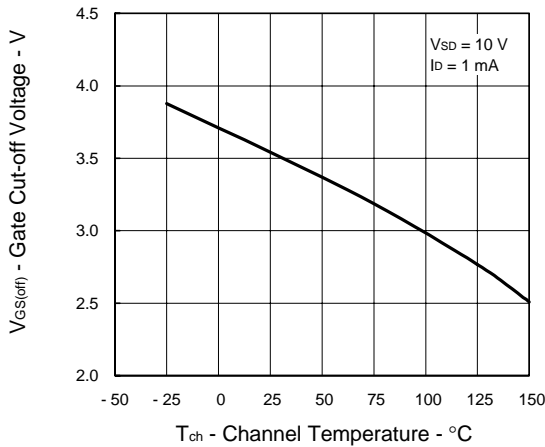
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



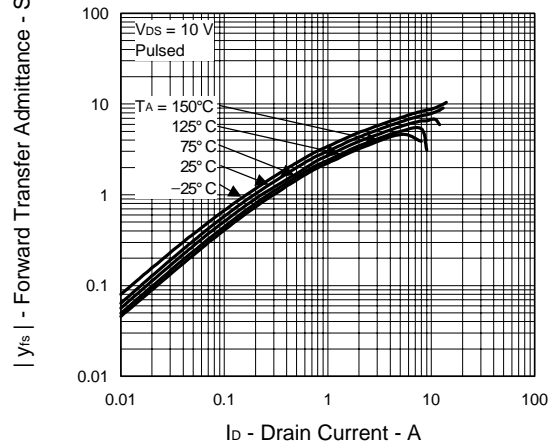
FORWARD TRANSFER CHARACTERISTICS



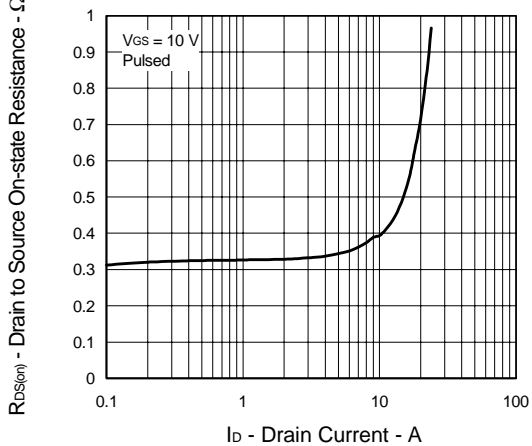
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



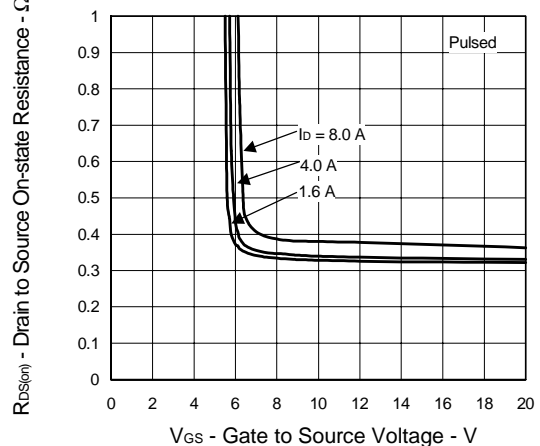
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



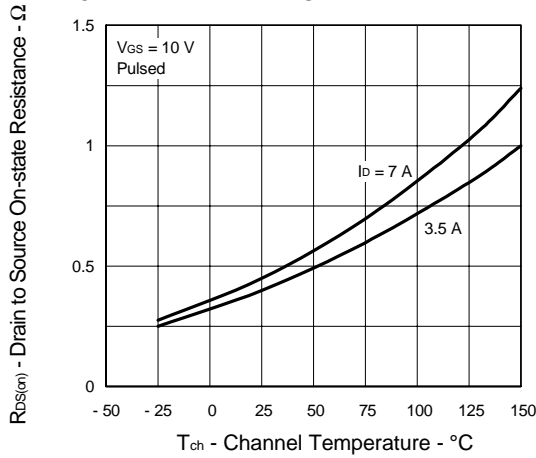
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



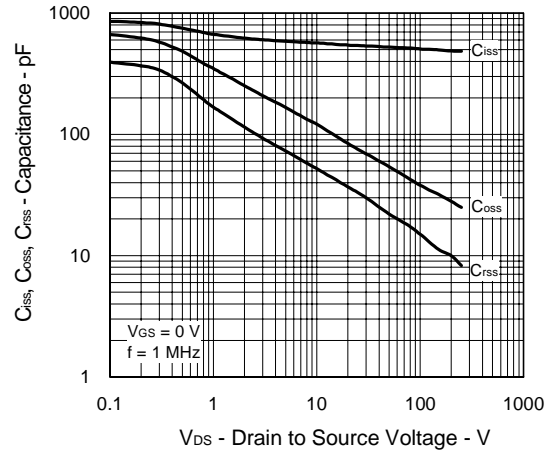
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



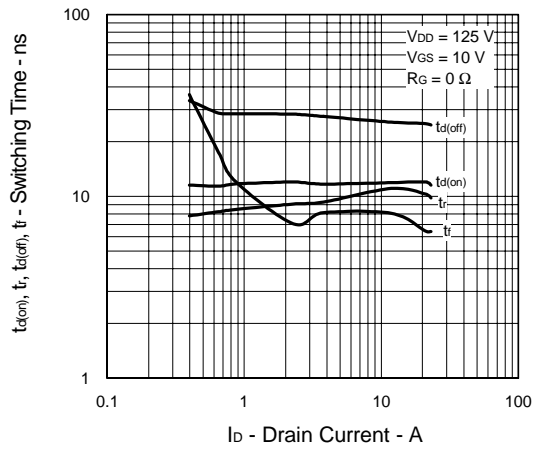
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



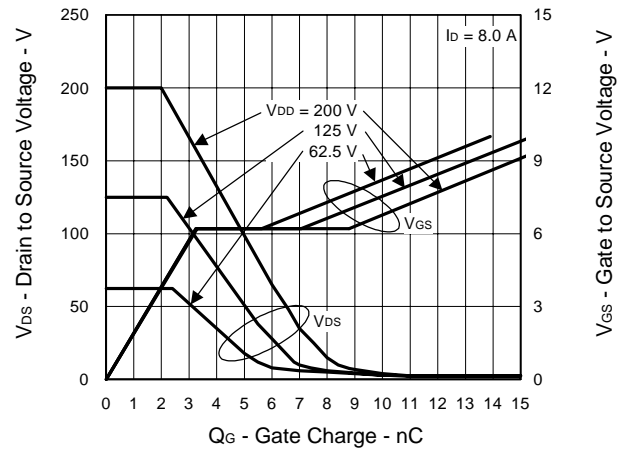
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



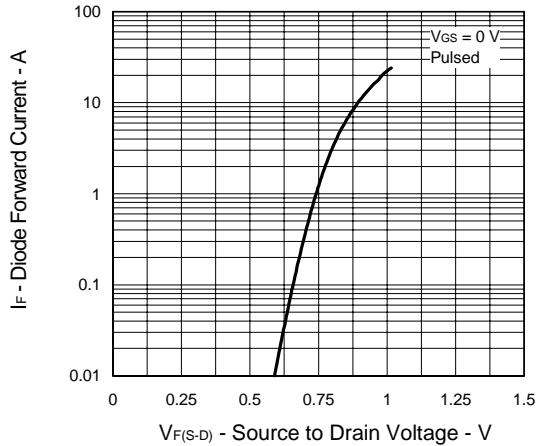
SWITCHING CHARACTERISTICS



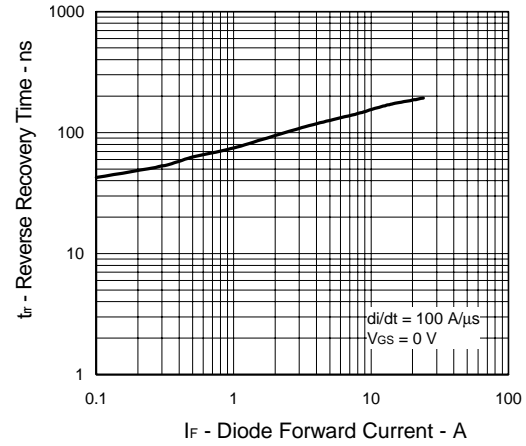
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



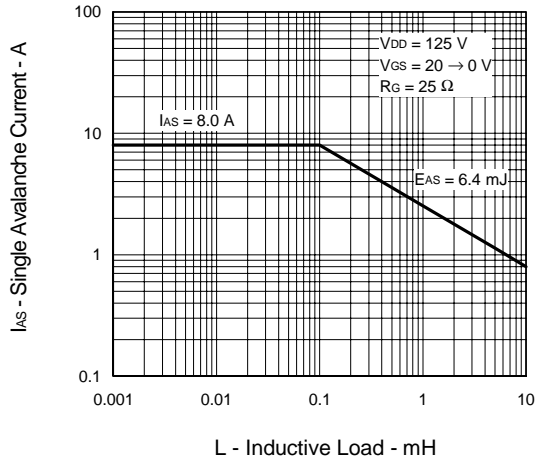
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



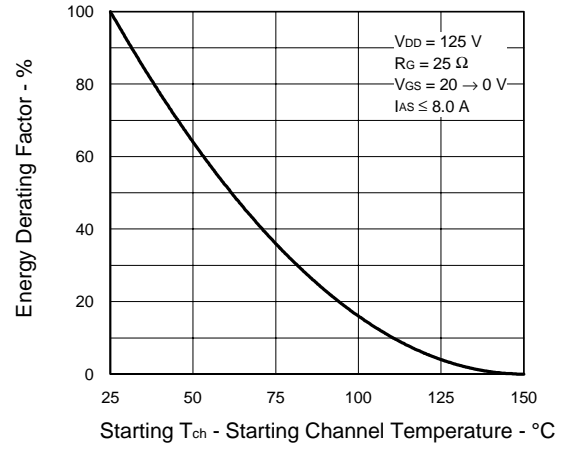
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



SINGLE AVALANCHE ENERGY DERATING FACTOR



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